

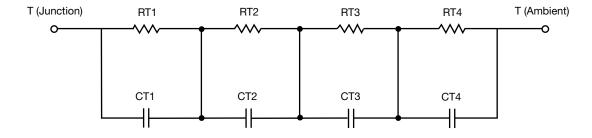
# **R-C Thermal Model Parameters**

### **DESCRIPTION**

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. R-C values for the electrical circuit in the Foster/tank and Cauer/filter configurations are included. When implemented in P-SPICE, these values have matching characteristic curves to the single-pulse transient thermal impedance curves for the MOSFET.

These RC values can be used in the P-SPICE simulation to evaluate the thermal behavior of the MOSFET junction temperature under a defined power profile. These techniques are described in application note AN609, "Thermal Simulation of Power MOSFETs on the P-SPICE Platform".

#### **R-C THERMAL MODEL FOR TANK CONFIGURATION**



R-C VALUES FOR TANK CONFIGURATION  THERMAL RESISTANCE (°C/W)					
RT1	N/A	63.9260m	N/A		
RT2	N/A	62.1259m	N/A		
RT3	N/A	70.5904m	N/A		
RT4	N/A	86.9237m	N/A		
	THERMAL CAPAC	CITANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CT1	N/A	787.6850m	N/A		
CT2	N/A	35.7874m	N/A		
CT3	N/A	24.1765m	N/A		
CT4	N/A	2.8805	N/A		

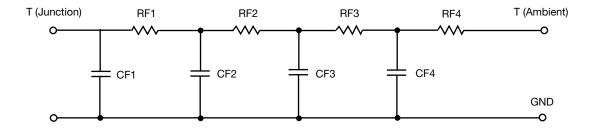
#### Note

• n/a indicates not applicable

This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.



## **R-C THERMAL MODEL FOR FILTER CONFIGURATION**



R-C VALUES FOR FILTER CONFIGURATION						
THERMAL RESISTANCE (°C/W)						
Junction to	Ambient	Case	Foot			
RF1	N/A	98.0906m	N/A			
RF2	N/A	55.2247m	N/A			
RF3	N/A	124.0347m	N/A			
RF4	N/A	2.6500m	N/A			
	THERMAL CAPAC	ITANCE (Joules/°C)				
Junction to	Ambient	Case	Foot			
CF1	N/A	12.9643m	N/A			
CF2	N/A	31.5662m	N/A			
CF3	N/A	1.0774	N/A			
CF4	N/A	1.4327	N/A			

### Note

• n/a indicates not applicable





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